

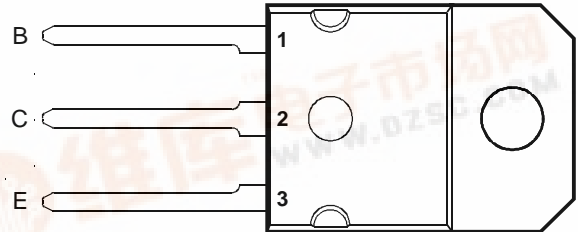
# BD545, BD545A, BD545B, BD545C NPN SILICON POWER TRANSISTORS

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- Designed for Complementary Use with the BD546 Series
- 85 W at 25°C Case Temperature
- 15 A Continuous Collector Current
- Customer-Specified Selections Available

SOT-93 PACKAGE  
(TOP VIEW)



Pin 2 is in electrical contact with the mounting base.

MDTRAA

### absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-base voltage ( $I_E = 0$ )	BD545	$V_{CBO}$	40	V
	BD545A		60	
	BD545B		80	
	BD545C		100	
Collector-emitter voltage ( $I_B = 0$ ) (see Note 1)	BD545	$V_{CEO}$	40	V
	BD545A		60	
	BD545B		80	
	BD545C		100	
Emitter-base voltage		$V_{EBO}$	5	V
Continuous collector current		$I_C$	15	A
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)		$P_{tot}$	85	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)		$P_{tot}$	3.5	W
Operating free air temperature range		$T_A$	-65 to +150	°C
Operating junction temperature range		$T_j$	-65 to +150	°C
Storage temperature range		$T_{stg}$	-65 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds		$T_L$	260	°C

- NOTES: 1. These values apply when the base-emitter diode is open circuited.  
 2. Derate linearly to 150°C case temperature at the rate of 0.68 W/°C.  
 3. Derate linearly to 150°C free air temperature at the rate of 28 mW/°C.



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## NPN SILICON POWER TRANSISTORS

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### electrical characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$ Collector-emitter breakdown voltage	$I_C = 30 \text{ mA}$ (see Note 4)	$I_B = 0$	BD545 BD545A BD545B BD545C	40 60 80 100			V
$I_{CES}$ Collector-emitter cut-off current	$V_{CE} = 40 \text{ V}$ $V_{CE} = 60 \text{ V}$ $V_{CE} = 80 \text{ V}$ $V_{CE} = 100 \text{ V}$	$V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$	BD545 BD545A BD545B BD545C			0.4 0.4 0.4 0.4	mA
$I_{CEO}$ Collector cut-off current	$V_{CE} = 30 \text{ V}$ $V_{CE} = 60 \text{ V}$	$I_B = 0$ $I_B = 0$	BD545/545A BD545B/545C			0.7 0.7	mA
$I_{EBO}$ Emitter cut-off current	$V_{EB} = 5 \text{ V}$	$I_C = 0$				1	mA
$h_{FE}$ Forward current transfer ratio	$V_{CE} = 4 \text{ V}$ $V_{CE} = 4 \text{ V}$ $V_{CE} = 4 \text{ V}$	$I_C = 1 \text{ A}$ $I_C = 5 \text{ A}$ $I_C = 10 \text{ A}$	(see Notes 4 and 5)	60 25 10			
$V_{CE(sat)}$ Collector-emitter saturation voltage	$I_B = 625 \text{ mA}$ $I_B = 2 \text{ A}$	$I_C = 5 \text{ A}$ $I_C = 10 \text{ A}$	(see Notes 4 and 5)			0.8 1	V
$V_{BE}$ Base-emitter voltage	$V_{CE} = 4 \text{ V}$	$I_C = 10 \text{ A}$	(see Notes 4 and 5)			1.8	V
$h_{fe}$ Small signal forward current transfer ratio	$V_{CE} = 10 \text{ V}$	$I_C = 0.5 \text{ A}$	$f = 1 \text{ kHz}$	20			
$ h_{fe} $ Small signal forward current transfer ratio	$V_{CE} = 10 \text{ V}$	$I_C = 0.5 \text{ A}$	$f = 1 \text{ MHz}$	3			

NOTES: 4. These parameters must be measured using pulse techniques,  $t_p = 300 \mu\text{s}$ , duty cycle  $\leq 2\%$ .

5. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

### thermal characteristics

PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$ Junction to case thermal resistance			1.47	°C/W
$R_{\theta JA}$ Junction to free air thermal resistance			35.7	°C/W

### resistive-load-switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS †			MIN	TYP	MAX	UNIT
$t_{on}$ Turn-on time	$I_C = 6 \text{ A}$	$I_{B(on)} = 0.6 \text{ A}$	$I_{B(off)} = -0.6 \text{ A}$		0.6		$\mu\text{s}$
$t_{off}$ Turn-off time	$V_{BE(off)} = -4 \text{ V}$	$R_L = 5 \Omega$	$t_p = 20 \mu\text{s}$ , dc $\leq 2\%$		1		$\mu\text{s}$

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

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## TYPICAL CHARACTERISTICS

**TYPICAL DC CURRENT GAIN  
VS  
COLLECTOR CURRENT**

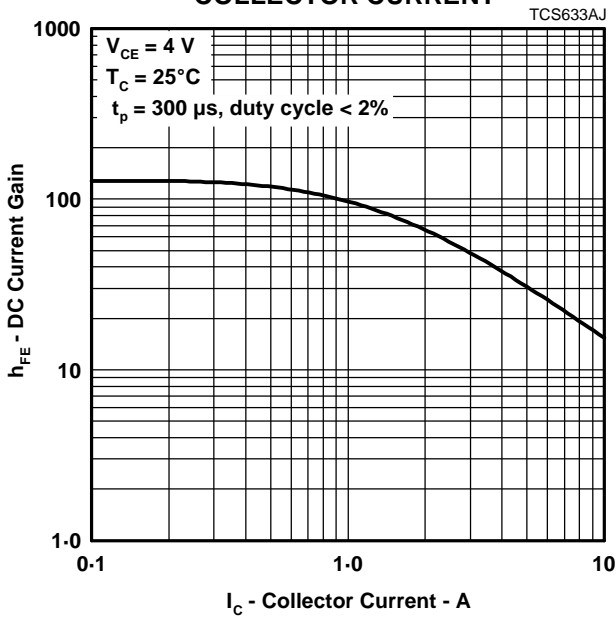


Figure 1.

**COLLECTOR-EMITTER SATURATION VOLTAGE  
VS  
BASE CURRENT**

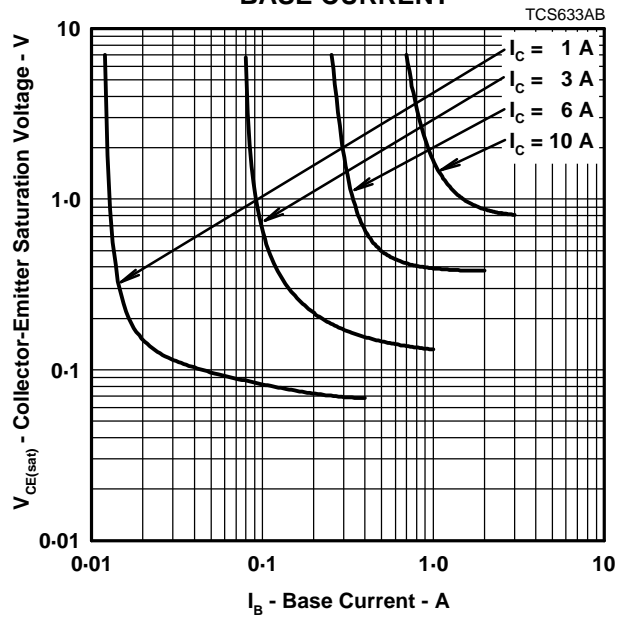


Figure 2.

**BASE-EMITTER VOLTAGE  
VS  
COLLECTOR CURRENT**

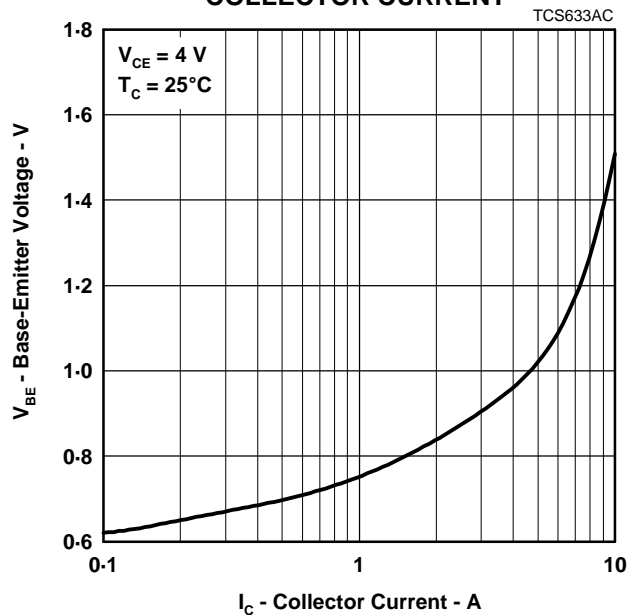


Figure 3.

# BD545, BD545A, BD545B, BD545C NPN SILICON POWER TRANSISTORS

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## MAXIMUM SAFE OPERATING REGIONS

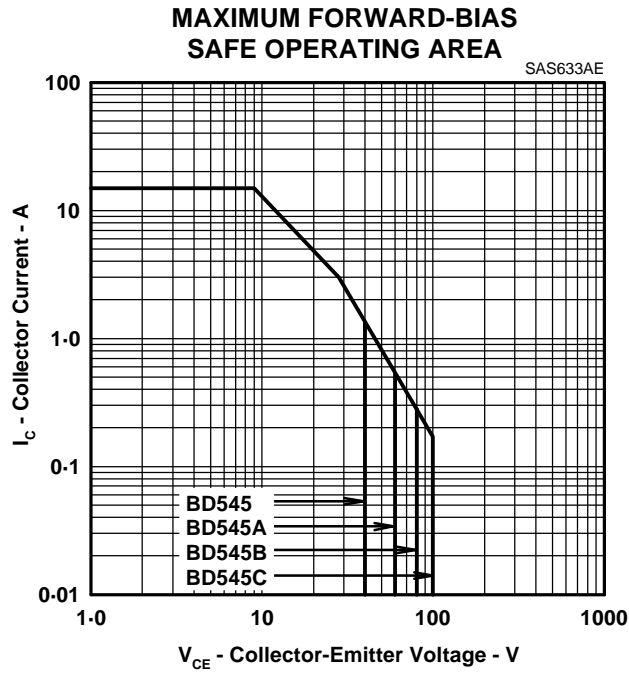


Figure 4.

## THERMAL INFORMATION

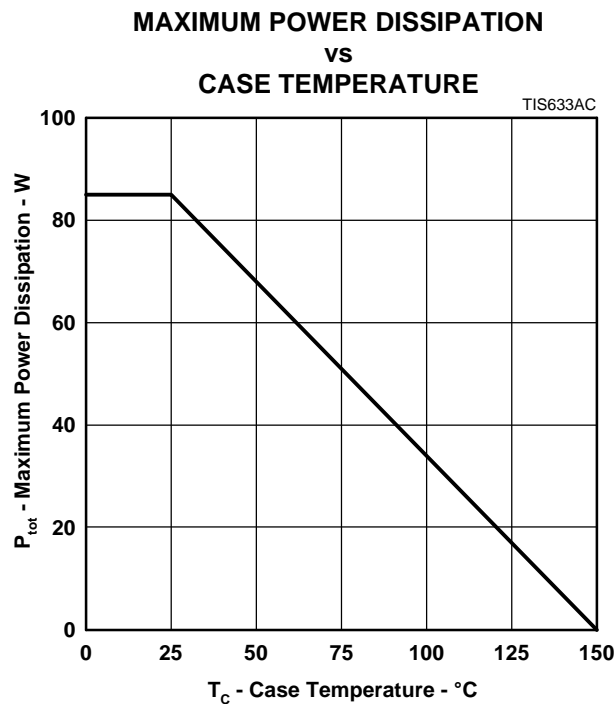


Figure 5.

# BD545, BD545A, BD545B, BD545C NPN SILICON POWER TRANSISTORS

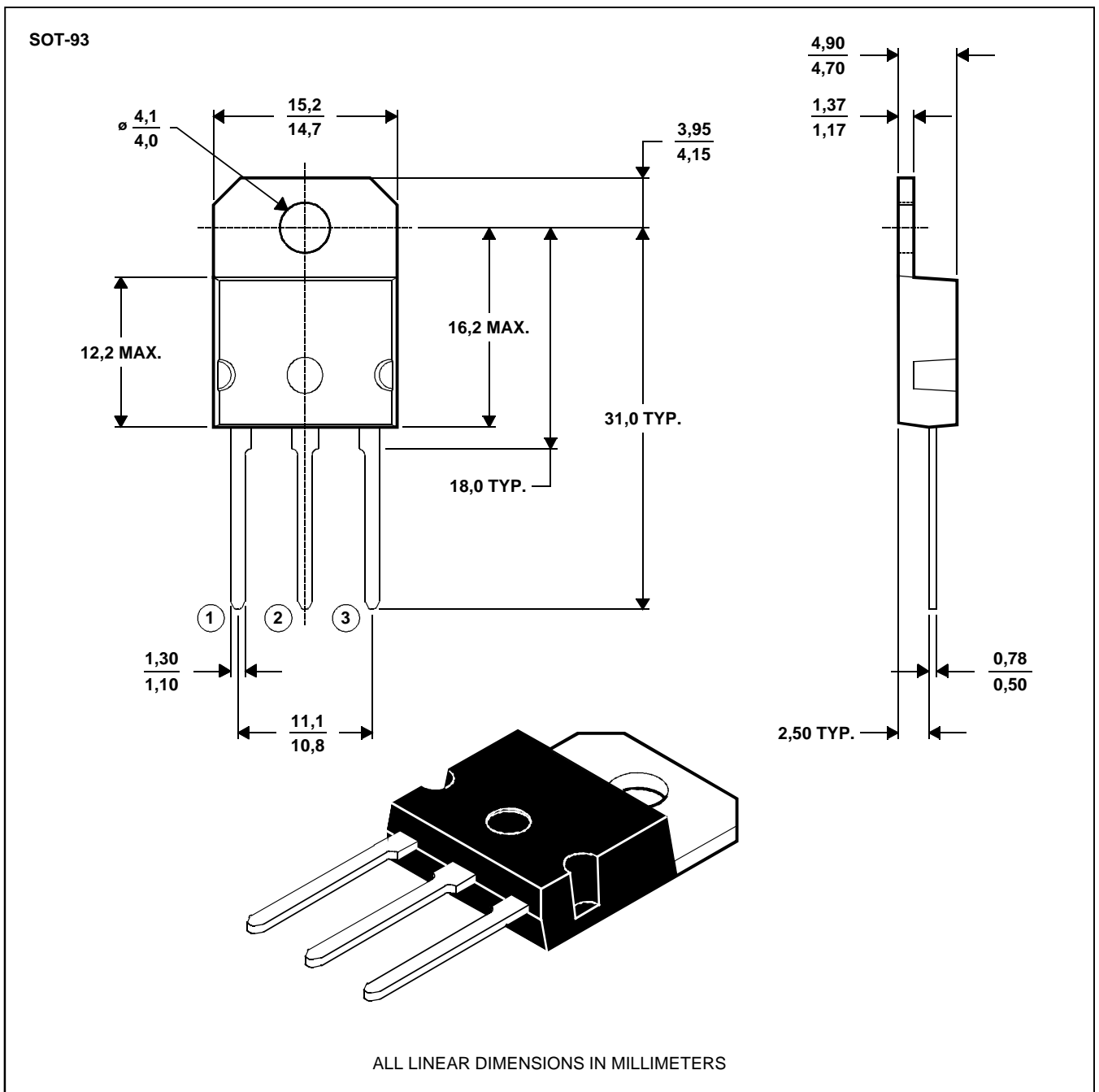
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## MECHANICAL DATA

### SOT-93

#### 3-pin plastic flange-mount package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



NOTE A: The centre pin is in electrical contact with the mounting tab.

MDXXAW

# **BD545, BD545A, BD545B, BD545C**

## **NPN SILICON POWER TRANSISTORS**

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